STS-310 PECVD Film Properties

	Deposition Rate (nm/min)	Refactive index (@632nm)	Etch rate in 6:1 BOE (nm/min)	Etch rate 20:1 HF (nm/min)	Stress (MPa)
High frequency oxide	**33**	**1.48**	**175**		**200 compressive**
Low frequency oxide	**43**	**1.48**	**95**	**65**	**350 compressive**
High frequency nitride	**10**	**2**	**30**		**400 tensile**
Low frequency nitride	**17**	**2**	**6**		**900 compressive**
Mixed frequency nitride	**11**	**2**	**25**		**60 tensile**
a-Silicon (Argon based)	**38**	**3.9**	**N/A**		**200 compressive**
a-Silicon (Nitrogen based)	**13**	**3.9**	**N/A**		**330 compressive**